



SANYO Semiconductors

## DATA SHEET

# MCH6649

P-Channel Silicon MOSFET  
**General-Purpose Switching Device**  
**Applications**

## Features

- 1.5V drive.
- Composite type with 2 MOSFETs contained in a single package, facilitating high-density mounting.

## Specifications

**Absolute Maximum Ratings** at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		-30	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±10	V
Drain Current (DC)	I <sub>D</sub>		-200	mA
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	-800	mA
Allowable Power Dissipation	P <sub>D</sub>	When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm) 1unit	0.6	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

**Electrical Characteristics** at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =-1mA, V <sub>GS</sub> =0V	-30			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V			-1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-100μA	-0.4		-1.4	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-100mA	190	320		mS
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =-100mA, V <sub>GS</sub> =-4V		1.8	2.4	Ω
	R <sub>DS(on)2</sub>	I <sub>D</sub> =-50mA, V <sub>GS</sub> =-2.5V		2.4	3.4	Ω
	R <sub>DS(on)3</sub>	I <sub>D</sub> =-10mA, V <sub>GS</sub> =-1.5V		4.5	9.0	Ω

Marking : XA

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**SANYO Semiconductor Co., Ltd.**

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

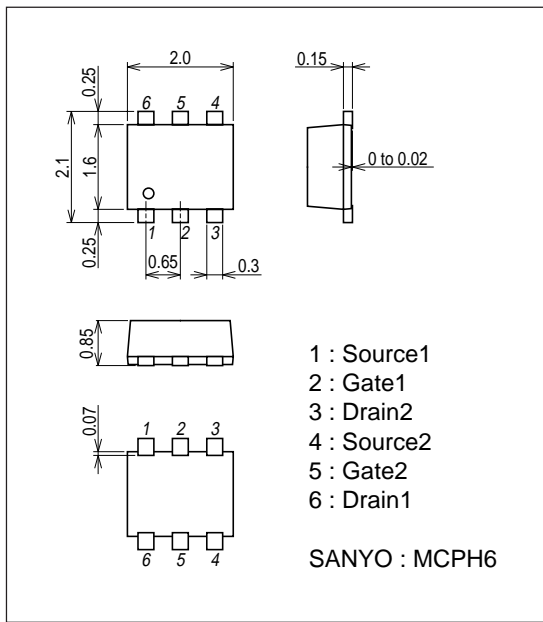
# MCH6649

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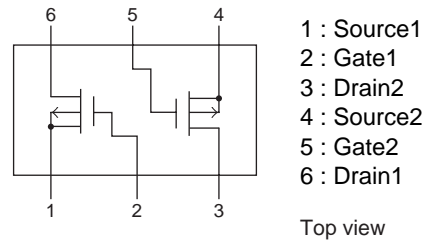
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	$C_{iss}$	$V_{DS}=-10V, f=1MHz$		35		pF
Output Capacitance	$C_{oss}$	$V_{DS}=-10V, f=1MHz$		7.2		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS}=-10V, f=1MHz$		2.1		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		75		ns
Rise Time	$t_r$	See specified Test Circuit.		170		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit.		550		ns
Fall Time	$t_f$	See specified Test Circuit.		350		ns
Total Gate Charge	$Q_g$	$V_{DS}=-10V, V_{GS}=-4V, I_D=-200mA$		0.58		nC
Gate-to-Source Charge	$Q_{gs}$	$V_{DS}=-10V, V_{GS}=-4V, I_D=-200mA$		0.17		nC
Gate-to-Drain "Miller" Charge	$Q_{gd}$	$V_{DS}=-10V, V_{GS}=-4V, I_D=-200mA$		0.12		nC
Diode Forward Voltage	$V_{SD}$	$I_S=-200mA, V_{GS}=0V$		-0.89	-1.2	V

## Package Dimensions

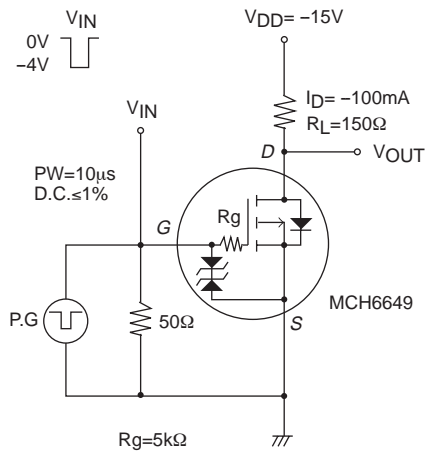
unit : mm (typ)  
7022A-006



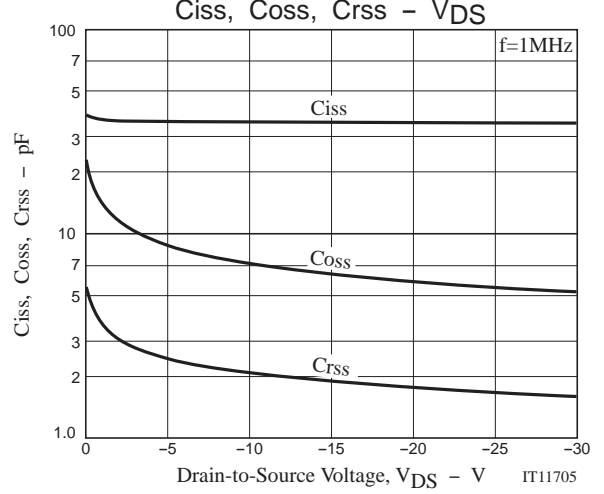
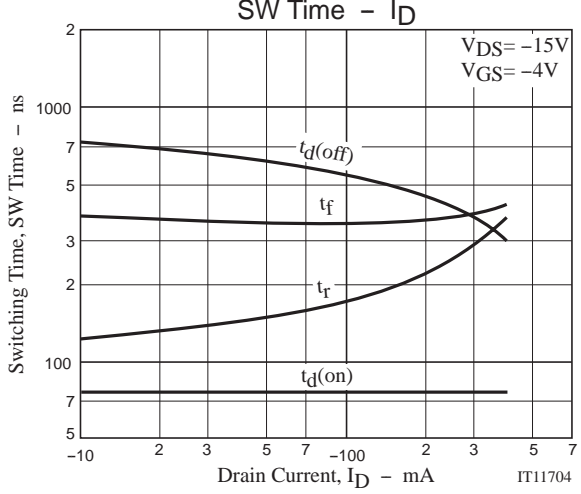
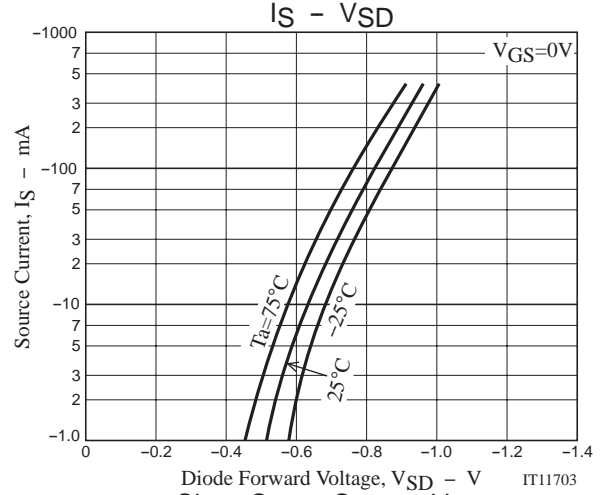
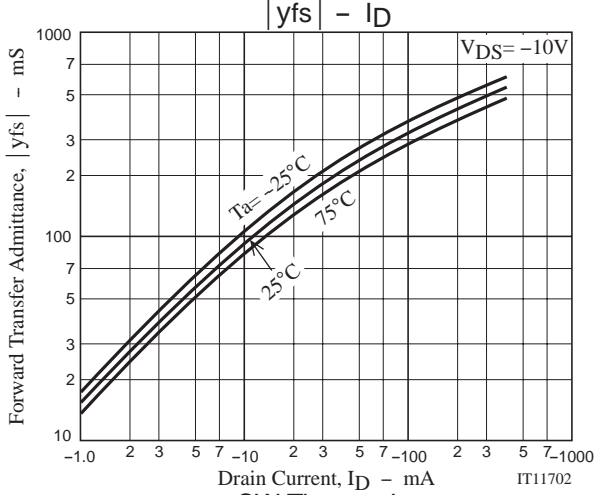
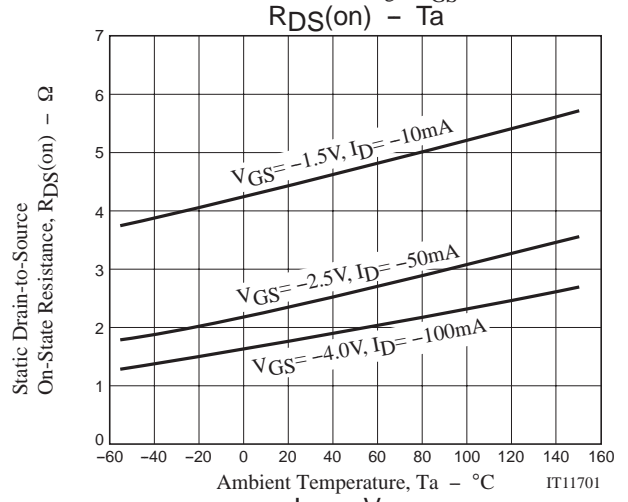
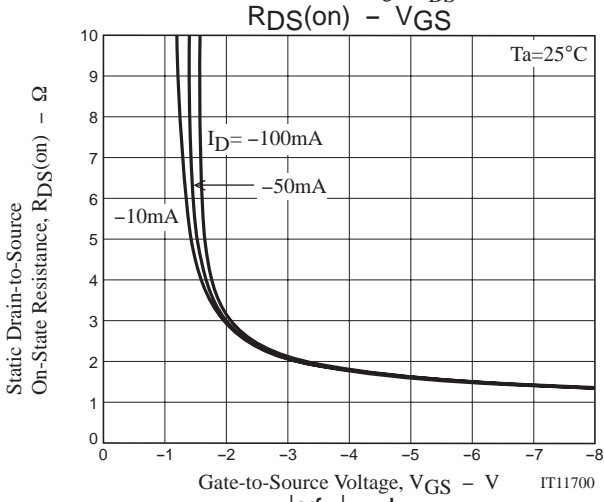
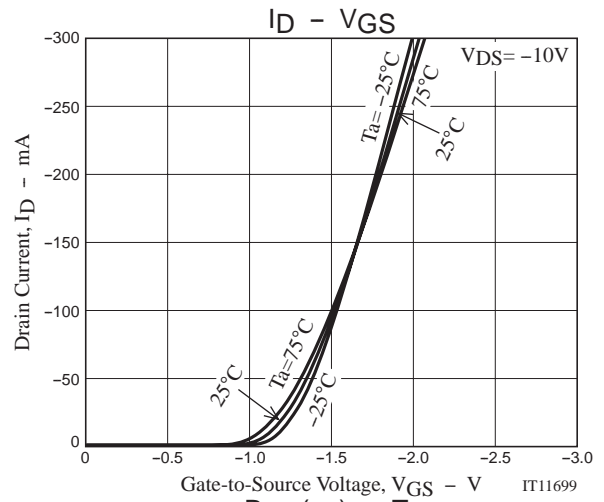
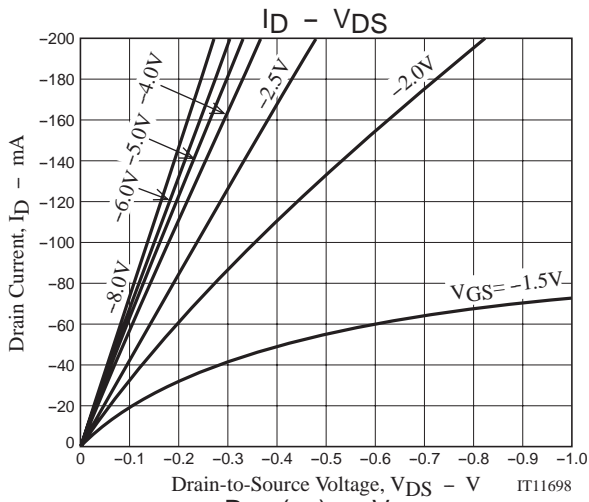
## Electrical Connection

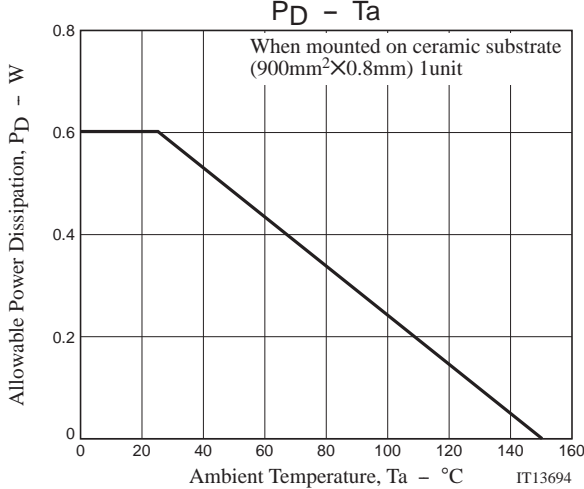
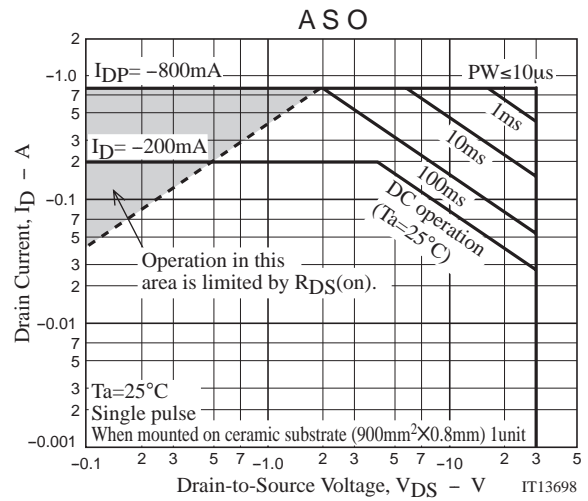
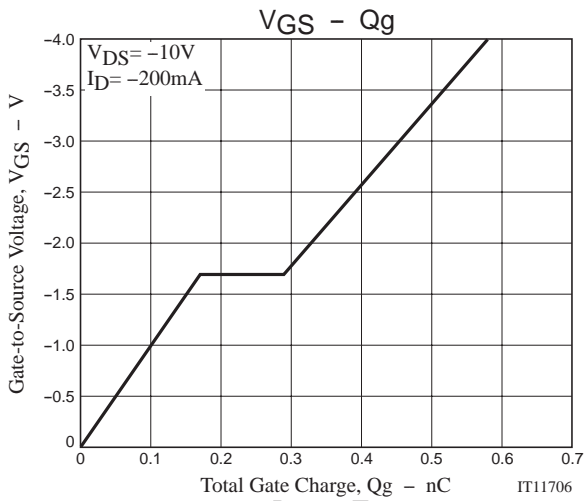


## Switching Time Test Circuit



# MCH6649





Note on usage : Since the MCH6649 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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